

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	19	("4048646" "4622569" "4701423" "4847212" "4849376" "4965218" "5528065" "5583368" "5773331" "6180477").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/13 16:19
L2	0	((dual-gate (dual adj gate)) with (FET (field adj effect adj transistor))) and (channel with ("2"\$nm angstrom)) and @pd>"20051029"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/13 16:21
L3	0	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with ("2"\$nm angstrom)) and @pd>"20051029"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/13 16:22
L4	0	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with ("2"\$nm angstrom)) and @pd>"20051029"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/13 16:22
L5	0	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with ("2"\$nm angstrom ".ANG.")) and @pd>"20051029"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/13 16:23
L6	465	257/296,368,347,377,413,618.ccls. and @pd>"20051029"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/13 16:35
L7	319	438/149,151,157,176,212.ccls. and @pd>"20051029"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/13 16:39
L8	0	(((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and ((sidewall spacer) with silicide)).clm.	US-PGPUB	OR	ON	2006/04/13 16:51
S1	8	("5844278") or ("6380078") or ("6180477") or ("5528065")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/13 16:19

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S2	14	((dual-gate (dual adj gate)) with (FET (field adj effect adj transistor))) and (channel with ("2"\$nm angstrom))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/13 16:21
S3	39	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with ("2"\$nm angstrom))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/13 16:22
S4	1	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with ("2"\$nm angstrom)) and (sidewall with silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 17:48
S5	39	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with ("2"\$nm angstrom))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/13 16:22
S6	39	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with ("2"\$nm angstrom ".ANG."))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/13 16:23
S7	11	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with ("2"\$nm angstrom "(.ANG.)") and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 08:02
S8	12	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with ("2"\$nm angstrom "(.ANG.)") and (silicide salicide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 08:02
S9	41	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and ((sidewall spacer) with silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/13 16:51
S10	1365	257/347,377,413,618.ccls. and @pd>"20030319"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 08:52
S11	3389	257/296.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 09:16

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S12	1389	257/296.ccls. and @pd<"19990518"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 09:30
S13	678	257/368.ccls. and @pd<"19990518"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 09:31
S14	1344	257/368.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 09:32

DWJ